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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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10/750,125

12/31/2003

James A. Kirchgessner

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7590

06/16/2005

Kenneth A. Nelson
Bryan Cave LLP
Suite 2200
Two North Central Avenue
Phoenix, AZ 85004-4406

EXAMINER

MANDALA, VICTOR A

ART UNIT

PAPER NUMBER

2826

DATE MAILED: 06/16/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

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Office Action Summary

Application No.	Applicant(s)	
10/750,125	KIRCHGESSNER, JAMES A.	
Examiner	Art Unit	
Victor A. Mandala Jr.	2826	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 31 December 2003.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-23 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☒ Claim(s) 11-19 is/are allowed.
- 6) ☒ Claim(s) 1,2,9,10,20,22 and 23 is/are rejected.
- 7) ☒ Claim(s) 3-8 and 21 is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 2, 9, and 10 are rejected under 35 U.S.C. 102(b) as being anticipated by U.S.

Patent No. 6,472,753 Kondo et al.

1. Referring to claim 1, a method of manufacturing a semiconductor component, the method comprising: providing a semiconductor substrate, (Figures 20a-e & 21a-c #1 and Col. 10 Lines 50-51), having a surface and a first conductivity type; forming a trench, (Figures 20a-e & 21a-c area of #6), in the surface of the semiconductor substrate, (Figures 20a-e & 21a-c #1), to define a plurality of active areas, (Figures 20a-e & 21a-c area of #3 & 5), separated from each other by the trench, (Figures 20a-e & 21a-c area of #6); forming a buried layer, (Figures 20a-e & 21a-c #4), in the semiconductor substrate, (Figures 20a-e & 21a-c #1), underneath a portion of the trench, (Figures 20a-e & 21a-c area of #6), wherein the buried layer, (Figures 20a-e & 21a-c #4 Col. 10 Lines 51-52), has a second conductivity type and is at least partially contiguous with the trench, (Figures 20a-e & 21a-c area of #6); after forming the buried layer, (Figures 20a-e & 21a-c #4), depositing an electrically insulating material in the trench, (Figures 20a-e & 21a-c #6);

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forming a collector region, (Figures 20a-e & 21a-c #5 Col. 10 Line 52), having the second conductivity type in one of the plurality of active areas, (Figures 20a-e & 21a-c area #5); forming a base structure having the first conductivity type, (Figures 20a-e & 21a-c #182 Col. 14 Lines 55-56), over the one of the plurality of active areas, (Figures 20a-e & 21a-c area of #5); and forming an emitter region, (Figures 20a-e & 21a-c #21 Col. 10 Line 58), having the second conductivity type over the one of the plurality of active areas, (Figures 20a-e & 21a-c area of #5), wherein; the collector region, (Figures 20a-e & 21a-c #5), forms a contact to the buried layer, (Figures 20a-e & 21a-c #4).

2. Referring to claim 2, a method wherein; the collector region, (Figures 20a-e & 21a-c #5 Col. 10 Line 52 Low doped*), has a first resistivity; the buried layer, (Figures 20a-e & 21a-c #4 Col. 10 Lines 51-52), has a second resistivity; and the first resistivity is greater than the second resistivity.

3. Referring to claim 9, a method, wherein; manufacturing the semiconductor component comprises: manufacturing the one of the plurality of active areas, (Figures 20a-e & 21a-c #5), to be symmetric, (partially symmetric up to the point where the left side insulative trench is buried deeper into the substrate), about a vertical line drawn through a middle of the emitter region, (Figures 20a-e & 21a-c #21).

4. Referring to claim 10, a semiconductor component, (Figure 21c), formed by the method of claim 1.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 20, 22, and 23 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 6,472,753 Kondo et al.

5. Referring to claim 20, a method of manufacturing a semiconductor component, the method comprising: providing a semiconductor substrate, (Figures 20a-e & 21a-c #1 and Col. 10 Lines 50-51), having a surface and a first conductivity type, where the semiconductor substrate, (Figures 20a-e & 21a-c #1), comprises a plurality of bipolar semiconductor regions, (Figures 20a-e & 21a-c area of #5 and see ** below), and a plurality of CMOS regions, (Figures 20a-e & 21a-c area of #9 and see ** below); forming a trench, (Figures 20a-e & 21a-c area of #6) in the surface of the semiconductor substrate, (Figures 20a-e & 21a-c #1), in the plurality of bipolar semiconductor regions, (Figures 20a-e & 21a-c area of #5 and see ** below), and in the plurality of CMOS regions, (Figures 20a-e & 21a-c area of #9 and see ** below), to define a plurality of active areas, (Figures 20a-e & 21a-c #3 & 5), separated from each other by the trench, (Figures 20a-e & 21a-c area of #6); forming a buried layer, (Figures 20a-e & 21a-c #4), in the semiconductor substrate, (Figures 20a-e & 21a-c #1), underneath a portion of the trench, (Figures 20a-e & 21a-c area of #6), in the plurality of bipolar semiconductor regions, (Figures 20a-e & 21a-c area of #5 and see ** below), where the buried layer has a second conductivity type, (Figures 20a-e & 21a-c #4 Col. 10 Lines 51-52), and is at least partially contiguous with the

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trench, (Figures 20a-e & 21a-c area of #6); after forming the buried layer, (Figures 20a-e & 21a-c #4 Col. 10 Lines 51-52), depositing an electrically insulating material in the trench, (Figures 20a-e & 21a-c #6); forming a collector region having the second conductivity type, (Figures 20a-e & 21a-c #5 Col. 10 Line 52 *Low doped*) in each one of the plurality of bipolar semiconductor regions, (Figures 20a-e & 21a-c area of #5 and see ** below); forming a base structure having the first conductivity type, (Figures 20a-e & 21a-c #182 Col. 14 Lines 55-56), over each one of the plurality of bipolar semiconductor regions, (Figures 20a-e & 21a-c area of #5 and see ** below); forming an emitter having the second conductivity type, (Figures 20a-e & 21a-c #21 Col. 10 Line 58), over each one of the plurality of bipolar semiconductor regions, (Figures 20a-e & 21a-c area of #5 and see ** below); forming source/drain regions, (Figures 20a-e & 21a-c #12), over each one of the plurality of CMOS regions, (Figures 20a-e & 21a-c area of #9 and see ** below); and forming a gate region, (Figures 20a-e & 21a-c #9), over each one of the plurality of CMOS regions, (Figures 20a-e & 21a-c area of #9 and see ** below), wherein: the collector region, (Figures 20a-e & 21a-c #5), forms a contact to the buried layer, (Figures 20a-e & 21a-c #4).

** Kondo et al. discloses the claimed invention except for the plurality of bipolar regions and plurality of cmos regions. It would have been obvious to one having skill in the art at the time the invention was made to have a plurality of bipolar and cmos regions, since it has been held that mere duplication of the essential working parts of a device involves only routine skill in the art. St. Regis Paper Co. vs Bomis Co. 193USPQ8

6. Referring to claim 22, a method, wherein: the collector region has a first resistivity, (Figures 20a-e & 21a-c #5 Col. 10 Line 52 *Low doped*); the buried layer has a second

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resistivity, (Figures 20a-e & 21a-c #4 Col. 10 Lines 51-52); and the first resistivity is greater than the second resistivity.

7. A semiconductor component formed by the method of claim 20, (Figure 21c).

Allowable Subject Matter

8. The following is a statement of reasons for the indication of allowable subject matter:

The prior art teaches a first conductivity semiconductor substrate having regions therein that are of the first and second conductivity, wherein a trench is formed in the substrate which defines a plurality of active regions, wherein a mask is formed to form buried regions of the second conductivity type in the substrate underneath the trench and where the trenches are filled with an insulative material, a collector region formed having the second conductivity, an emitter formed having the second conductivity, wherein the collector contacts the buried layer. The prior art does not teach the above teachings in combination with the trenches having spacers formed therein and where the buried layer is self aligned with the trench and spacers, which are later removed before depositing the insulative material. This combination has been found to be non-obvious thus novel.

9. Claims 11-19 are allowed.

10. Claims 3-8 and 21 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

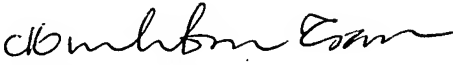
Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Victor A. Mandala Jr. whose telephone number is (571) 272-1918. The examiner can normally be reached on Monday through Thursday from 8am till 6pm..

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J. Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

VAMJ
6/8/05


Minhloan Tran
Primary Examiner
Art Unit 2826